

## SOT-363 Plastic-Encapsulate Transistors

### UMX1N DUAL TRANSISTOR (NPN+NPN)

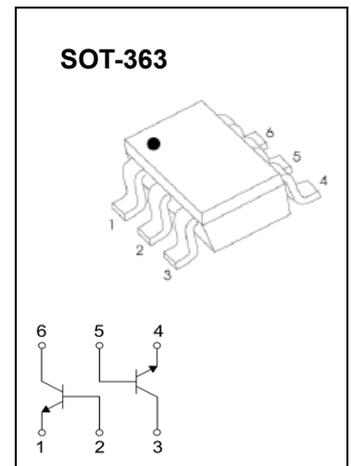
#### FEATURES

- Two 2SC2412K chips in a SOT-363 package
- Mounting possible with SOT-363 automatic mounting machines
- Transistor elements are independent, eliminating interference
- Mounting cost and area can be cut in half

#### MARKING:X1

#### MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	60	V
$V_{CEO}$	Collector-Emitter Voltage	50	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current -Continuous	150	mA
$P_C$	Collector Power Dissipation	150	mW
$T_J$	Junction Temperature	150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^{\circ}\text{C}$



#### ELECTRICAL CHARACTERISTICS ( $T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=50\mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=50\mu\text{A}, I_C=0$	7			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=60\text{V}, I_E=0$			0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=7\text{V}, I_C=0$			0.1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE}=6\text{V}, I_C=1\text{mA}$	120		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.4	V
Transition frequency	$f_T$	$V_{CE}=12\text{V}, I_C=2\text{mA}, f=100\text{MHz}$		180		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=12\text{V}, I_E=0, f=1\text{MHz}$		2.0	3.5	pF